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Kind regards,

Team Nexperia



# PHK5NQ15T

N-channel TrenchMOS standard level FET

2 August 2013

Product data sheet

## 1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

## 2. Features and benefits

- Low conduction losses due to low on-state resistance

## 3. Applications

- DC-to-DC convertors switching
- General purpose switching

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$ ; $T_j \leq 150\text{ }^\circ\text{C}$	-	-	150	V
$I_D$	drain current	$T_{sp} = 25\text{ }^\circ\text{C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 3</a>	-	-	5	A
$P_{tot}$	total power dissipation	$T_{sp} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	-	-	6.25	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>	-	56	75	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 5\text{ A}$ ; $V_{DS} = 75\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	12	-	nC

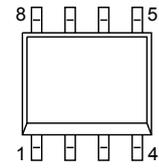
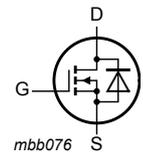


Scan or click this QR code to view the latest information for this product



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>SO8 (SOT96-1)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
5	D	drain		
6	D	drain		
7	D	drain		
8	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHK5NQ15T	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHK5NQ15T	K5NQ15T

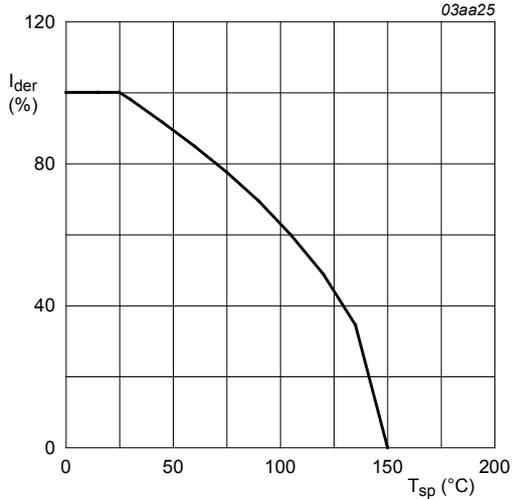
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

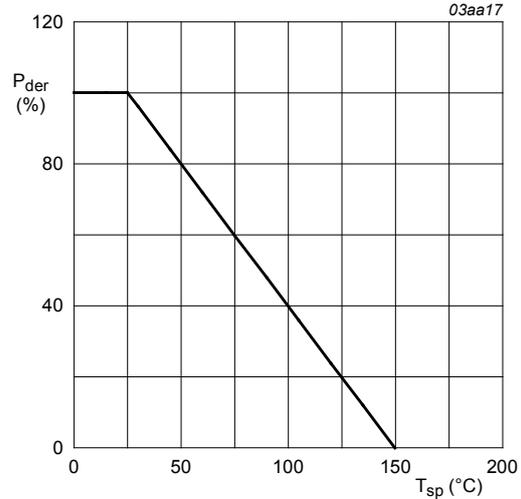
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 150\text{ °C}$	-	150	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 150\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	150	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$T_{sp} = 100\text{ °C}; V_{GS} = 10\text{ V}; \text{Fig. 1}$	-	3.23	A
		$T_{sp} = 25\text{ °C}; V_{GS} = 10\text{ V}; \text{Fig. 1}; \text{Fig. 3}$	-	5	A
$I_{DM}$	peak drain current	$T_{sp} = 25\text{ °C}; \text{pulsed}; t_p \leq 10\text{ }\mu\text{s}; \text{Fig. 3}$	-	20	A
$P_{tot}$	total power dissipation	$T_{sp} = 25\text{ °C}; \text{Fig. 2}$	-	6.25	W

Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-55	150	°C
T <sub>j</sub>	junction temperature		-55	150	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C	-	5	A
I <sub>SM</sub>	peak source current	T <sub>sp</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs	-	20	A



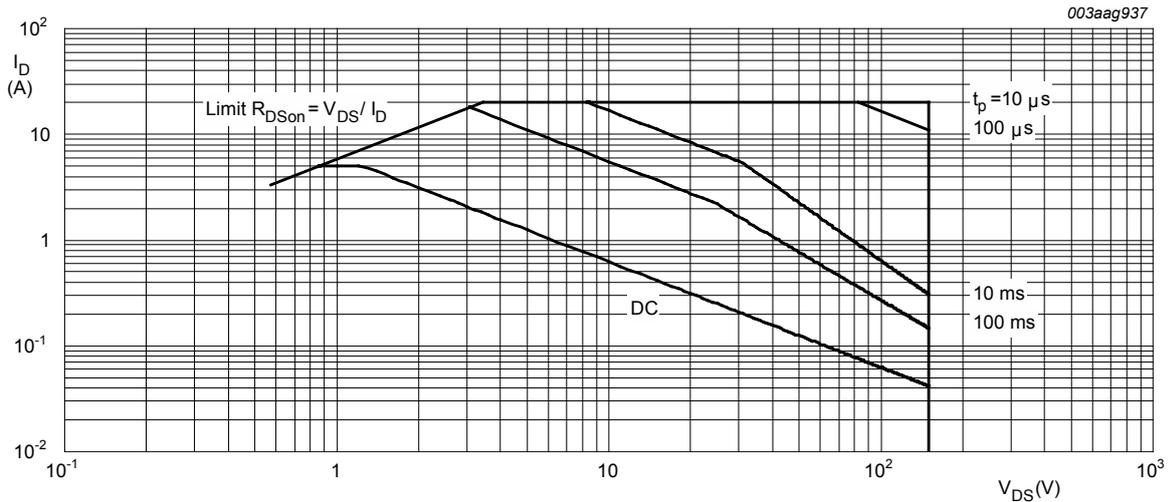
**Fig. 1. Normalized continuous drain current as a function of solder point temperature**

$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$



**Fig. 2. Normalized total power dissipation as a function of solder point temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$



**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

*T<sub>mb</sub> = 25°C; I<sub>DM</sub> is a single pulse*

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	<a href="#">Fig. 4</a>	-	-	20	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint ; mounted on printed-circuit board	-	70	-	K/W

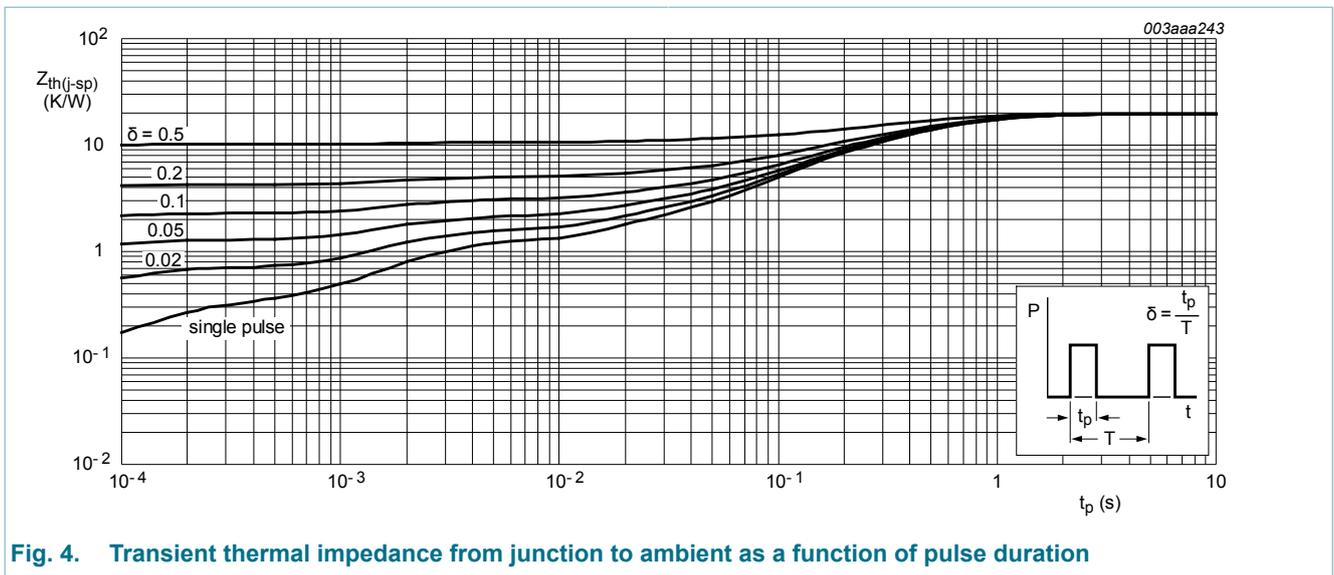


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration

### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	134	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	150	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$ <a href="#">Fig. 8</a>	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 8</a>	1.2	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 8</a>	2	3	4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 120 V; V_{GS} = 0 V; T_j = 150 \text{ }^\circ C$	-	-	100	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	10	100	nA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = -10\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	10	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 150\text{ }^\circ\text{C};$ <a href="#">Fig. 9; Fig. 10</a>	-	129	173	mΩ
		$V_{GS} = 5\text{ V}; I_D = 3\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	60	80	mΩ
		$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9;</a> <a href="#">Fig. 10</a>	-	56	75	mΩ
$R_G$	gate resistance	$f = 1\text{ MHz}$	-	1.9	3.8	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 5\text{ A}; V_{DS} = 75\text{ V}; V_{GS} = 10\text{ V};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	29	41	nC
$Q_{GS}$	gate-source charge		-	3	-	nC
$Q_{GD}$	gate-drain charge		-	12	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 12</a>	-	1150	1553	pF
$C_{oss}$	output capacitance		-	187	252	pF
$C_{rss}$	reverse transfer capacitance		-	61	85	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 75\text{ V}; R_L = 15\text{ }^\Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 6\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}; I_D = 5\text{ A}$	-	12	-	ns
$t_r$	rise time		-	12	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
$t_f$	fall time		-	18	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 5\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 13</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 5\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 90\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	87	113	ns
$Q_r$	recovered charge		-	162	-	nC

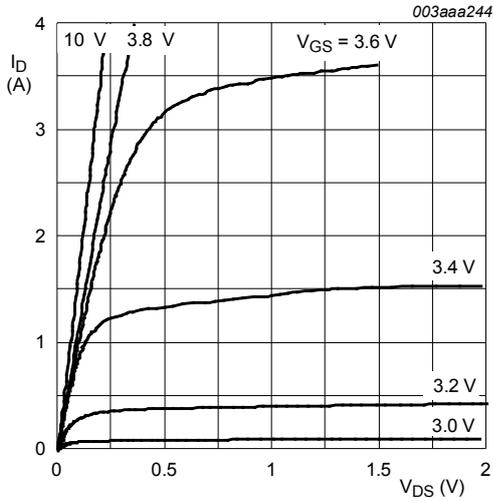


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

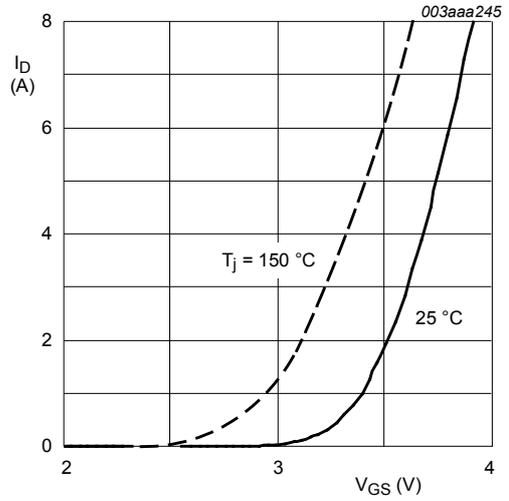


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}; V_{DS} > I_D \times R_{DS(on)}$

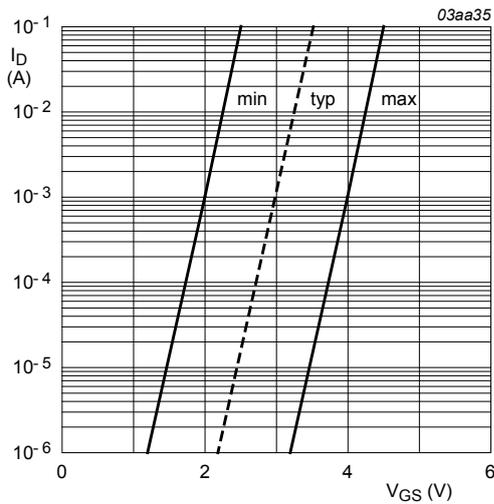


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

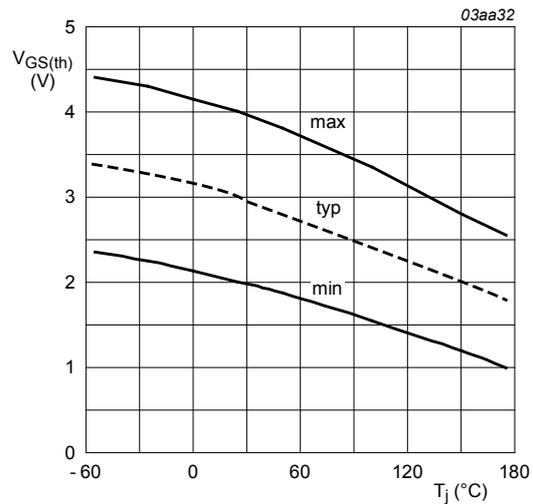
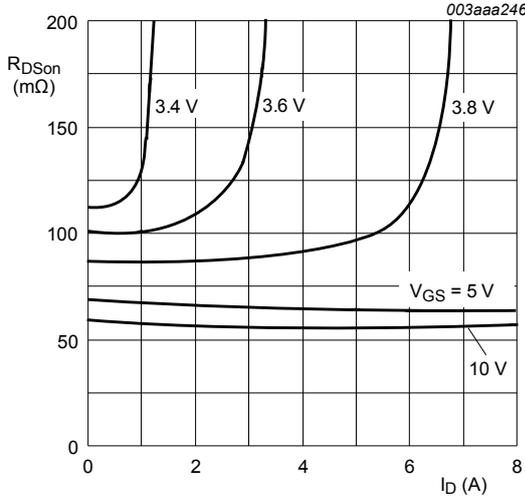


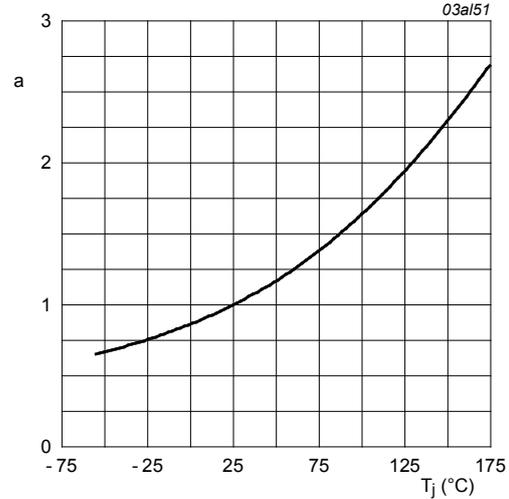
Fig. 8. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{mA}; V_{DS} = V_{GS}$



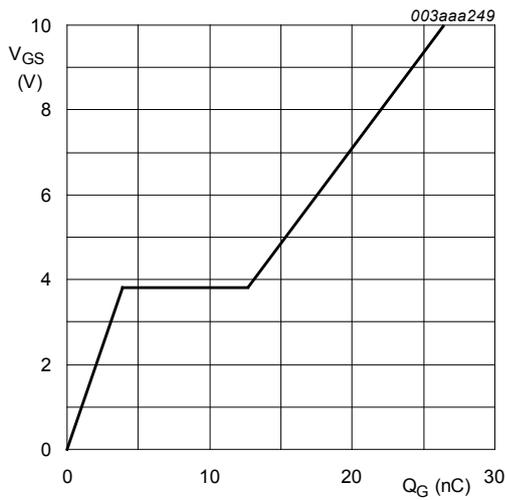
**Fig. 9. Drain-source on-state resistance as a function of drain current; typical values**

$$T_j = 25^\circ\text{C}$$



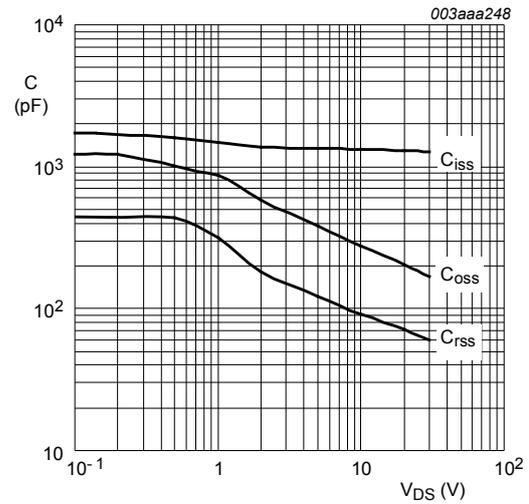
**Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{Dson}}{R_{Dson(25^\circ\text{C})}}$$



**Fig. 11. Gate-source voltage as a function of gate charge; typical values**

$$I_D = 5\text{A}; V_{DD} = 75\text{V}$$



**Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

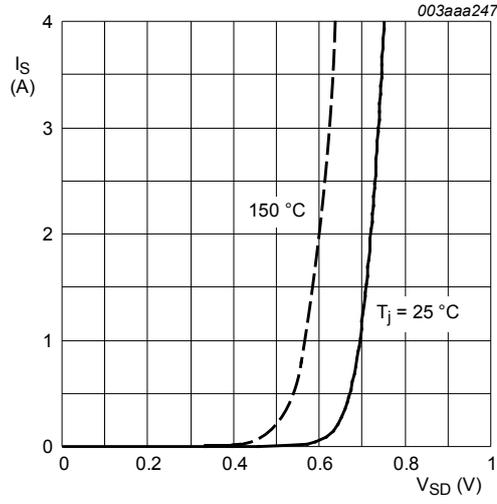


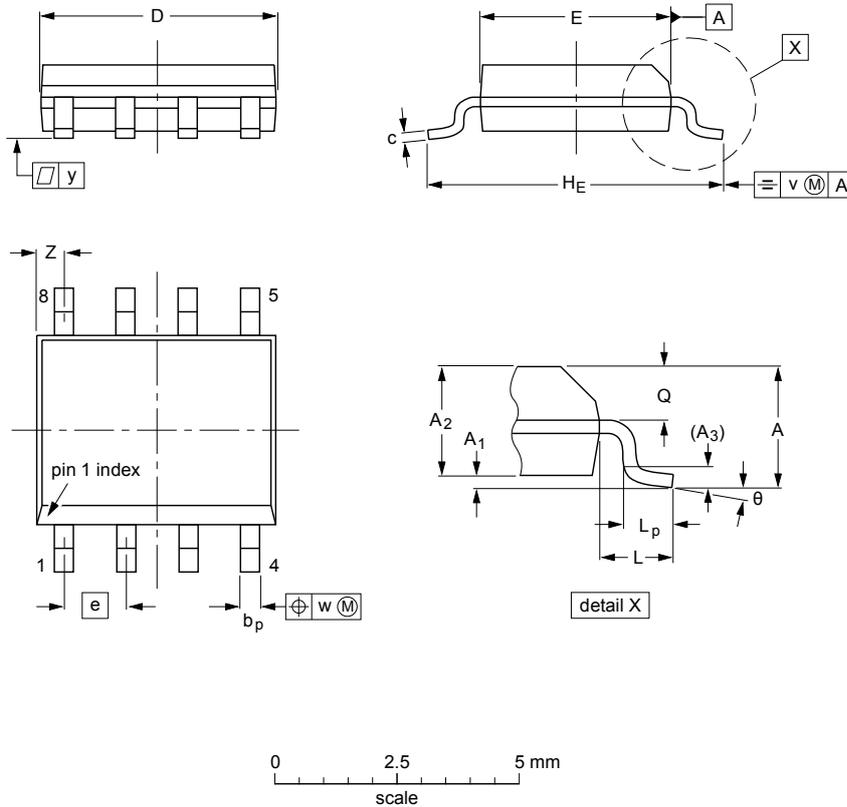
Fig. 13. Source current as a function of source-drain voltage; typical values

$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}$ ;  $V_{GS} = 0\text{V}$

### 11. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



**DIMENSIONS** (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(2)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

**Notes**

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT96-1	076E03	MS-012				99-12-27-03-02-18

Fig. 14. Package outline SO8 (SOT96-1)

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 2 August 2013